L Number	Hits	Search Text	DB	Time stamp
1	30156	(single near crystal\$4) near3 substrate	USPAT;	2004/10/30 15:34
			US-PGPUB;	
	l.		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	13563	((single near crystal\$4) near3 substrate) and (opening or vias	USPAT;	2004/10/30 15:37
		or cavity or trench or groove)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	4408	(((single near crystal\$4) near3 substrate) and (opening or	USPAT;	2004/10/30 15:37
		vias or cavity or trench or groove)) and isolation	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	ŀ		IBM_TDB	
4	866	relaxed same defect\$1	USPAT;	2004/10/30 15:39
			US-PGPUB;	
,			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
5	260	(relaxed same defect\$1) and strained	USPAT;	2004/10/30 15:39
			US-PGPUB;	
		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	189	((relaxed same defect\$1) and strained) and transistor	USPAT;	2004/10/30 15:39
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_		L.,,	IBM_TDB	
7	92	(((single near crystal\$4) near3 substrate) and (opening or	USPAT;	2004/10/30 15:40
		vias or cavity or trench or groove)) and (relaxed same	US-PGPUB;	
		defect\$1)	EPO; JPO;	
			DERWENT;	
	F.4	////single man emotel@4) man 2 collector() and (IBM_TDB	0004/10/00 45 45
8	51	((((single near crystal\$4) near3 substrate) and (opening or	USPAT;	2004/10/30 15:40
		vias or cavity or trench or groove)) and (relaxed same	US-PGPUB;	
		defect\$1)) and strained	EPO; JPO;	
			DERWENT;	
l :			IBM_TDB	1